Product data sheet

1. General description

NPN low V_{CEsat} Breakthrough in Smal Signal (BISS) transitor in a medium power SOT89 (SC-62) flat lead Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- · High energy efficiency due to less heat generation
- AEC-Q101 qualified

3. Applications

- DC-to-DC conversion
- Supply line switches
- Battery charger
- LCD backlighting
- Driver in low supply voltage applications (e.g. lamps and LEDs)
- · Inductive load driver (e.g. relays, buzzers and motors)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base		_	_	60	V
I _C	collector current			-	-	1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	2	Α
h _{FE}	DC current gain	V_{CE} = 10 V; I_{C} = 500 mA; T_{amb} = 25 °C	[1]	170	-	360	

[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		С
2	С	collector		В
3	В	base	3 2 1	E
			SOT89	sym123

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBSS4160X	SOT89	plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	SOT89		

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS4160X	S41

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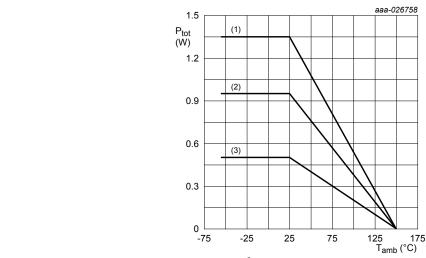
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	60	V
V_{CEO}	collector-emitter voltage	open base		-	60	V
V _{EBO}	emitter-base voltage	open collector		-	7	V
I _C	collector current			-	1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	2	Α
I _B	base current			-	300	mA
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	1	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	500	mW
			[2]	-	950	mW
			<u>[3]</u>	-	1.35	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated; mounting pad for collector 1 cm². Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated; mounting pad for collector 6 cm².



- (1) FR4 PCB, single-sided copper, 6 cm²
- (2) FR4 PCB, single-sided copper, 1 cm²
- (3) FR4 PCB, single-sided copper, standard footprint

Fig. 1. Power derating curves

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
f	thermal resistance	in free air	[1]	-	-	250	K/W
	from junction to ambient		[2]	-	-	132	K/W
			[3]	-	-	93	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated; mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated; mounting pad for collector 6 cm².

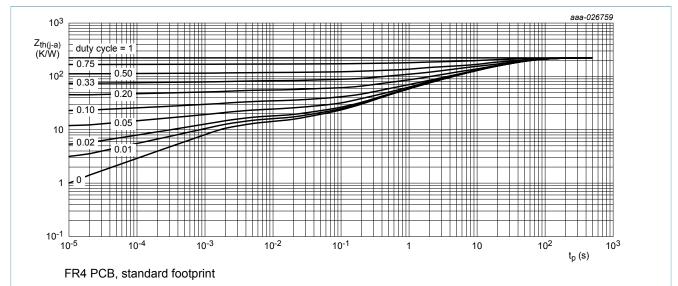


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

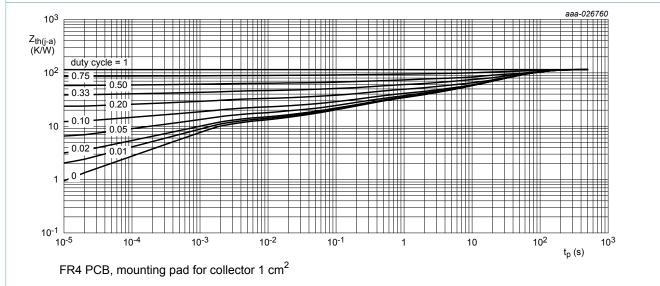
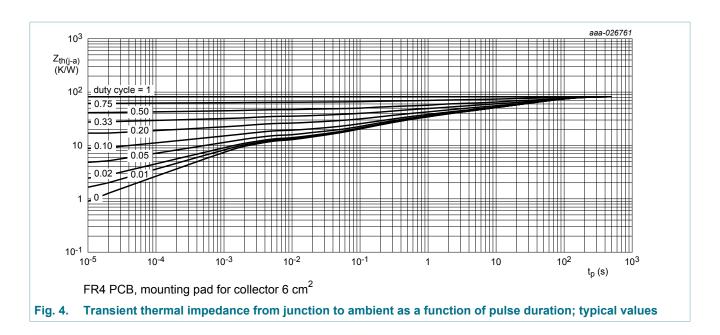


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 48 V; I _E = 0 A; T _{amb} = 25 °C		-	-	100	nA
	current	V _{CB} = 48 V; I _E = 0 A; T _j = 150 °C		-	-	10	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = 48 V; V _{BE} = 0 V; T _{amb} = 25 °C		-	-	100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 10 V; I_{C} = 500 mA; T_{amb} = 25 °C	[1]	170	-	360	
		V _{CE} = 5 V; I _C = 1 A; T _{amb} = 25 °C	[1]	50	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 500 \text{ mA}; I_B = 50 \text{ mA}; T_{amb} = 25 \text{ °C}$	[1]	-	-	200	mV
R _{CEsat}	collector-emitter saturation resistance			-	-	0.4	Ω
V _{BEsat}	base-emitter saturation voltage		[1]	-	-	1.2	V
V_{BE}	base-emitter voltage	V _{CE} = 5 V; I _C = 1 A; T _{amb} = 25 °C	[1]	-	-	1	V
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 50 mA; f = 100 MHz; T_{amb} = 25 °C		-	180	-	MHz
C _c	collector capacitance	V _{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C		-	6	-	pF

[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02$

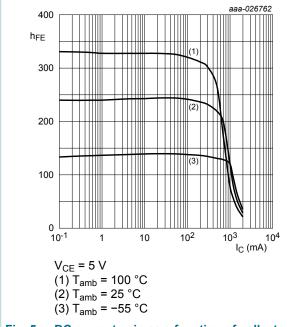


Fig. 5. DC current gain as a function of collector current; typical values

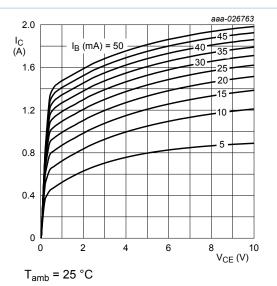


Fig. 6. Collector current as a function of collectoremitter voltage; typical values

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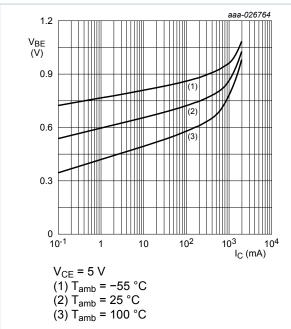


Fig. 7. Base-emitter voltage as a function of collector current; typical values

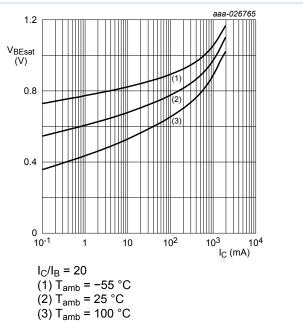
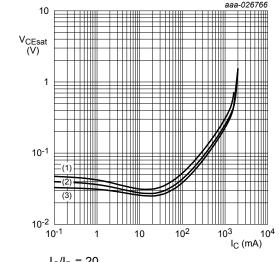
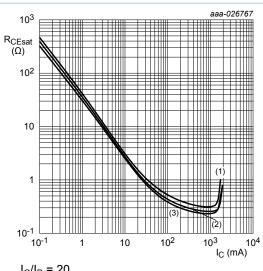


Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$ (1) $T_{\rm amb} = 100~{\rm ^{\circ}C}$ (2) $T_{\rm amb} = 25~{\rm ^{\circ}C}$ (3) $T_{\rm amb} = -55~{\rm ^{\circ}C}$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

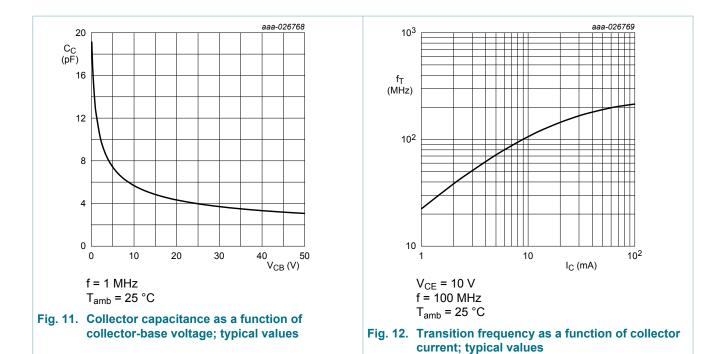


 $I_{C}/I_{B} = 20$ (1) $T_{amb} = 100 \,^{\circ}C$ (2) $T_{amb} = 25 \,^{\circ}C$ (3) $T_{amb} = -55 \,^{\circ}C$

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

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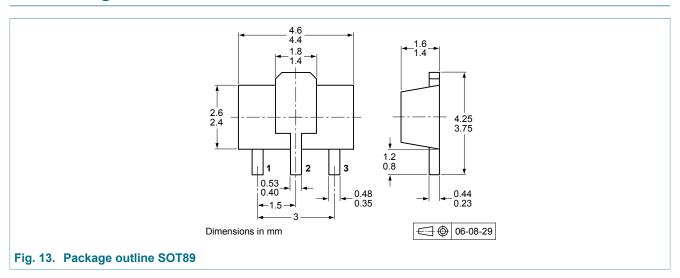


11. Test information

Quality information

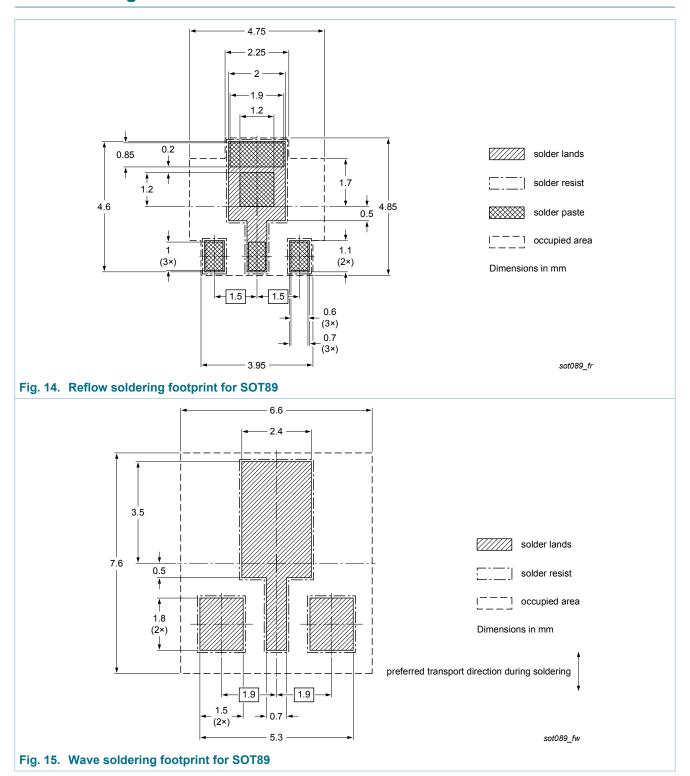
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4160X v.1	20170523	Product data sheet	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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	Features and benefits

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